

2SD662, 2SD662B

Silicon NPN epitaxial planer type

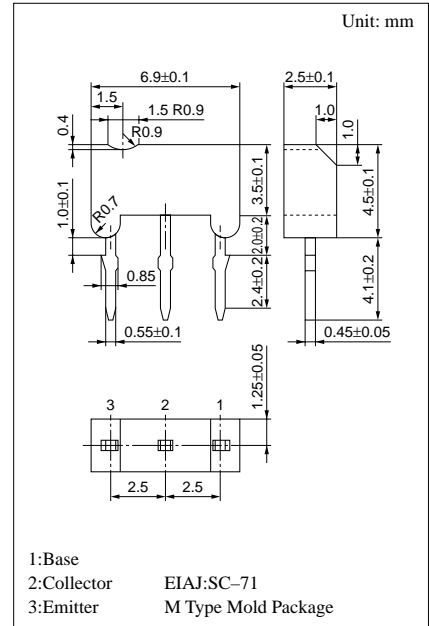
For high breakdown voltage general amplification

Features

- High collector to emitter voltage V_{CEO} .
- High transition frequency f_T .
- M type package allowing easy automatic and manual insertion as well as stand-alone fixing to the printed circuit board.

Absolute Maximum Ratings (Ta=25°C)

Parameter	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	250	V
2SD662		400	
Collector to emitter voltage	V_{CEO}	200	V
2SD662B		400	
Emitter to base voltage	V_{EBO}	5	V
Peak collector current	I_{CP}	100	mA
Collector current	I_C	70	mA
Collector power dissipation	P_C	600	mW
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-55 ~ +150	°C



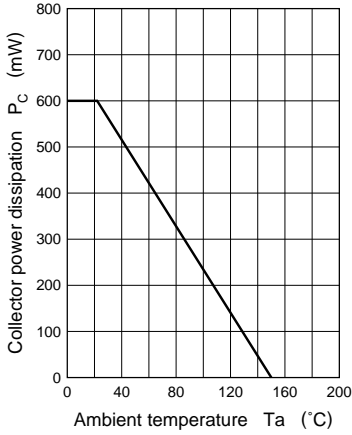
Electrical Characteristics (Ta=25°C)

Parameter	Symbol	Conditions	min	typ	max	Unit
Collector cutoff current	I_{CEO}	$V_{CE} = 100V, I_B = 0$			2	μA
Collector to emitter voltage	2SD662	V_{CEO}	$I_C = 100\mu A, I_B = 0$	200		V
	2SD662B			400		
Emitter to base voltage	V_{EBO}	$I_E = 10\mu A, I_C = 0$	5			V
Forward current transfer ratio	2SD662	h_{FE}^*	$V_{CE} = 10V, I_C = 5mA$	30		220
	2SD662B			30		150
Collector to emitter saturation voltage	$V_{CE(sat)}$	$I_C = 50mA, I_B = 5mA$			1.2	V
Transition frequency	f_T	$V_{CB} = 10V, I_E = -10mA, f = 200MHz$	50	80		MHz
Collector output capacitance	C_{ob}	$V_{CB} = 10V, I_E = 0, f = 1MHz$		5	10	pF

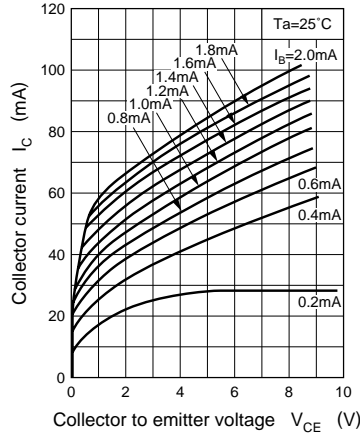
* h_{FE} Rank classification

Rank	P	Q	R
h_{FE}	30 ~ 100	60 ~ 150	100 ~ 220

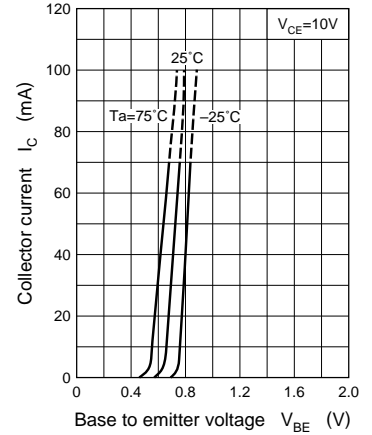
$P_C - T_a$



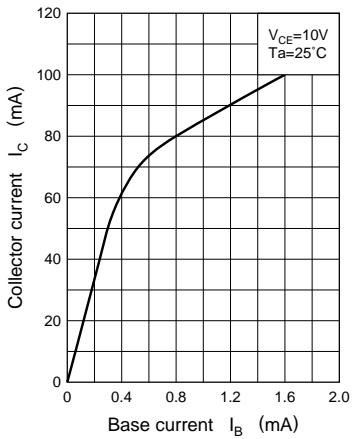
$I_C - V_{CE}$



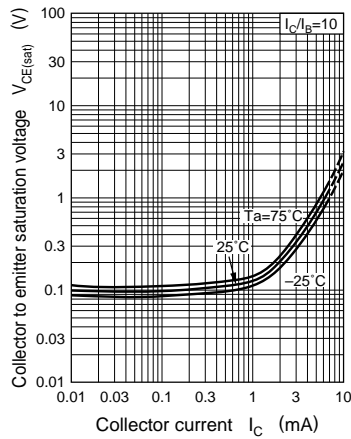
$I_C - V_{BE}$



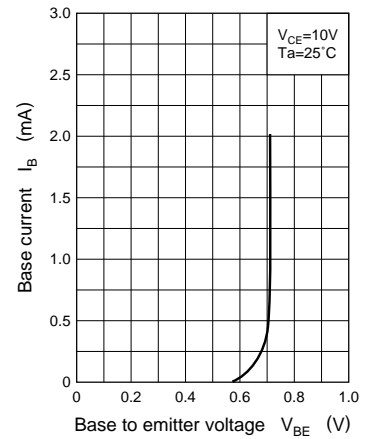
$I_C - I_B$



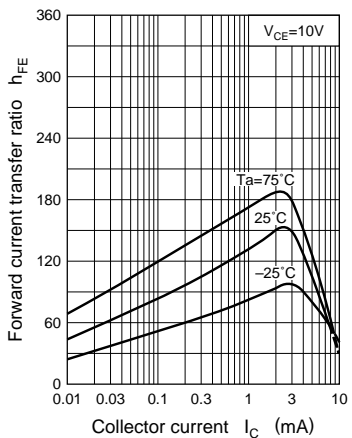
$V_{CE(sat)} - I_C$



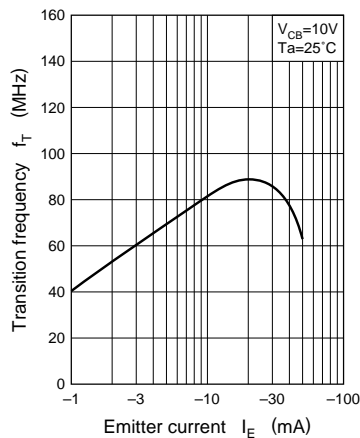
$I_B - V_{BE}$



$h_{FE} - I_C$



$f_T - I_E$



$I_{CBO} - T_a$

